



TB0640M - TB3500M

50A BI-DIRECTIONAL SURFACE MOUNT THYRISTOR SURGE PROTECTIVE DEVICE

NEW PRODUCT

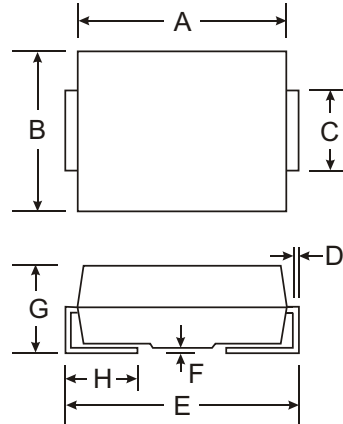
Features

50A Peak Pulse Current @ 10/1000 s
250A Peak Pulse Current @ 8/20 s
58 - 320V Stand-Off Voltages
Oxide-Glass Passivated Junction
Bi-Directional Protection In a Single Device
High Off-State impedance and Low On-State Voltage

Mechanical Data

Case: SMB, Molded Plastic
Plastic Material: UL Flammability
Classification Rating 94V-0
Moisture sensitivity: Level 1 per J-STD-020A
Terminals: Solder Plated Terminal -
Solderable per MIL-STD-202, Method 208
Polarity: None; Bi-Directional Devices Have No
Polarity Indicator
Weight: 0.093 grams (approx.)
Marking: Date Code and Marking Code (See Page 4)
Ordering Information: See Page 4

UNDER DEVELOPMENT



| SMB | | |
|----------------------|------|------|
| Dim | Min | Max |
| A | 4.06 | 4.57 |
| B | 3.30 | 3.94 |
| C | 1.96 | 2.21 |
| D | 0.15 | 0.31 |
| E | 5.21 | 5.59 |
| F | 0.05 | 0.20 |
| G | 2.01 | 2.62 |
| H | 0.76 | 1.52 |
| All Dimensions in mm | | |

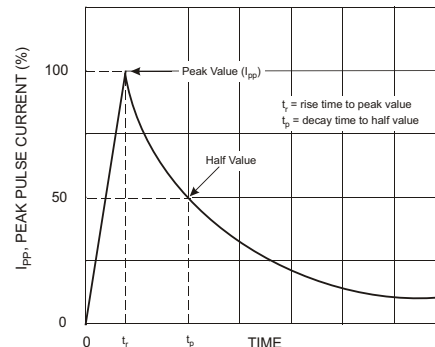
Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

| Characteristic | Symbol | Value | Unit |
|--|-------------|-------------|---------------------|
| Non-Repetitive Peak Impulse Current @ 10/1000us | I_{PP} | 50 | A |
| Non-Repetitive Peak On-State Current @ 8.3ms (one-half cycle) | I_{TSM} | 30 | A |
| Junction Temperature Range | T_J | -40 to +150 | C |
| Storage Temperature Range | T_{STG} | -55 to +150 | C |
| Thermal Resistance, Junction to Lead | R_{JL} | 20 | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction to Ambient | R_{JA} | 100 | $^\circ\text{C/W}$ |
| Typical Positive Temperature Coefficient for Breakdown Voltage | VBR / T_J | 0.1 | $\%/^\circ\text{C}$ |

Maximum Rated Surge Waveform

| Waveform | Standard | I_{PP} (A) |
|------------|----------------|--------------|
| 2/10 us | GR-1089-CORE | 300 |
| 8/20 us | IEC 61000-4-5 | 250 |
| 10/160 us | FCC Part 68 | 150 |
| 10/700 us | ITU-T, K20/K21 | 100 |
| 10/560 us | FCC Part 68 | 75 |
| 10/1000 us | GR-1089-CORE | 50 |

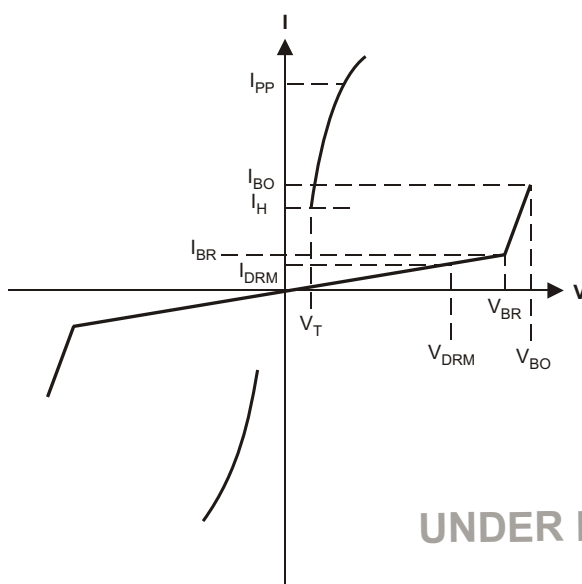


Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

| Part Number | Rated Repetitive Off-State Voltage | Off-State Leakage Current @ V_{DRM} | Breakover Voltage | On-State Voltage @ $I_T = 1\text{A}$ | Breakover Current I_{BO} | | Holding Current I_{H} | | Off-State Capacitance | Marking Code |
|-------------|------------------------------------|--|---------------------|--------------------------------------|-----------------------------------|----------|--------------------------------|----------|-----------------------|--------------|
| | V_{DRM} (V) | I_{DRM} (μA) | V_{BO} (V) | V_{T} (V) | Min (mA) | Max (mA) | Min (mA) | Max (mA) | C_{O} (pF) | |
| TB0640M | 58 | 5 | 77 | 3.5 | 50 | 800 | 150 | 800 | 140 | T064M |
| TB0720M | 65 | 5 | 88 | 3.5 | 50 | 800 | 150 | 800 | 140 | T072M |
| TB0900M | 75 | 5 | 98 | 3.5 | 50 | 800 | 150 | 800 | 140 | T090M |
| TB1100M | 90 | 5 | 130 | 3.5 | 50 | 800 | 150 | 800 | 90 | T110M |
| TB1300M | 120 | 5 | 160 | 3.5 | 50 | 800 | 150 | 800 | 90 | T130M |
| TB1500M | 140 | 5 | 180 | 3.5 | 50 | 800 | 150 | 800 | 90 | T150M |
| TB1800M | 160 | 5 | 220 | 3.5 | 50 | 800 | 150 | 800 | 90 | T180M |
| TB2300M | 190 | 5 | 265 | 3.5 | 50 | 800 | 150 | 800 | 60 | T230M |
| TB2600M | 220 | 5 | 300 | 3.5 | 50 | 800 | 150 | 800 | 60 | T260M |
| TB3100M | 275 | 5 | 350 | 3.5 | 50 | 800 | 150 | 800 | 60 | T310M |
| TB3500M | 320 | 5 | 400 | 3.5 | 50 | 800 | 150 | 800 | 60 | T350M |

| Symbol | Parameter |
|------------------|--------------------------------------|
| V_{DRM} | Stand-off Voltage |
| I_{DRM} | Leakage current at stand-off voltage |
| V_{BR} | Breakdown voltage |
| I_{BR} | Breakdown current |
| V_{BO} | Breakover voltage |
| I_{BO} | Breakover current |
| I_{H} | Holding current NOTE: 1 |
| V_{T} | On state voltage |
| I_{PP} | Peak pulse current |
| C_{O} | Off-state capacitance NOTE: 2 |

- Notes:
1. $I_{\text{H}} > (V_{\text{L}}/R_{\text{L}})$ If this criterion is not obeyed, the TSPD triggers but does not return correctly to high-resistance state. The surge recovery time does not exceed 30ms.
 2. Off-state capacitance measured at $f = 1.0\text{MHz}$, $1.0V_{\text{RMS}}$ signal, $V_{\text{R}} = 2V_{\text{DC}}$ bias.



UNDER DEVELOPMENT

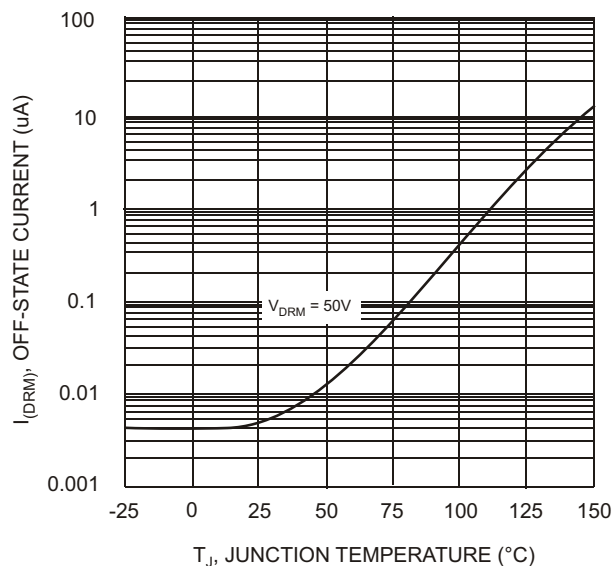


Fig. 1 Off-State Current vs. Junction Temperature

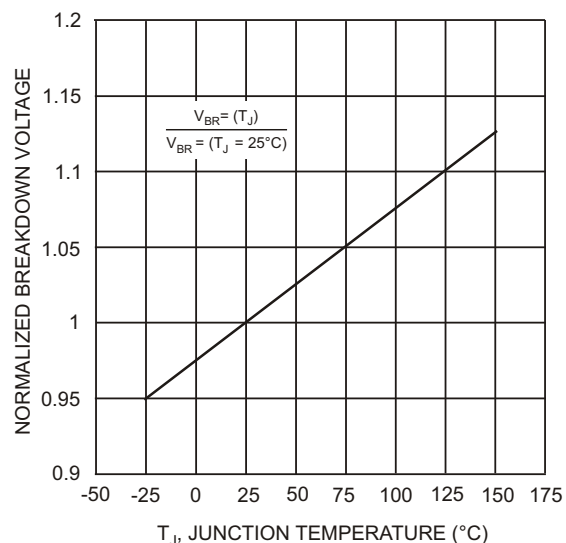


Fig. 2 Relative Variation of Breakdown Voltage vs. Junction Temperature

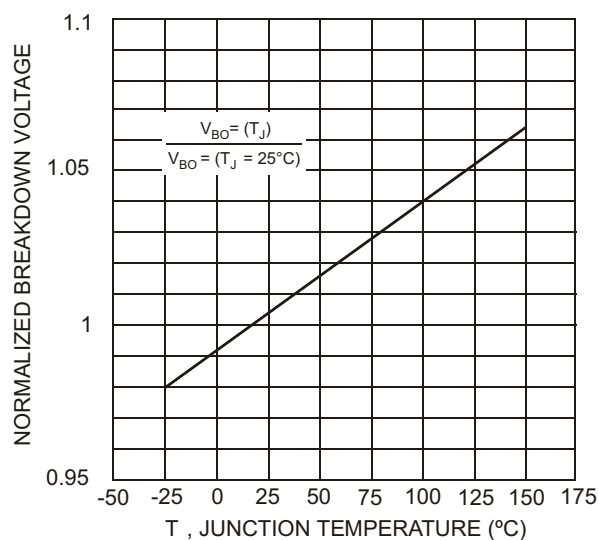


Fig. 3 Relative Variation of Breakover Voltage vs. Junction Temperature

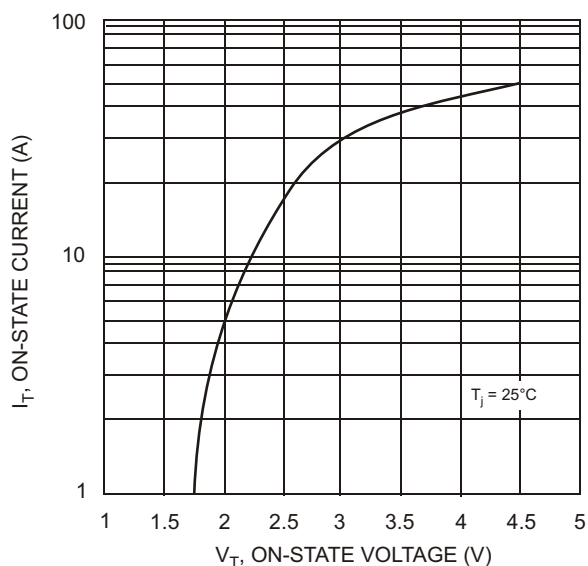


Fig. 4 On-State Current vs. On-State Voltage

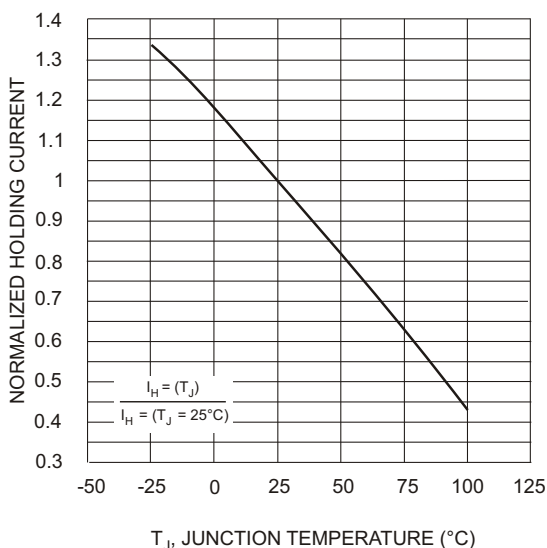


Fig. 5 Relative Variation of Holding Current vs. Junction Temperature

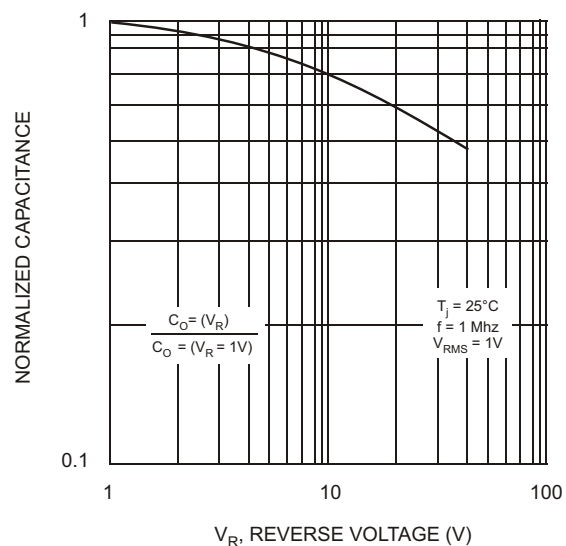


Fig. 6 Relative Variation of Junction Capacitance vs. Reverse Voltage Bias

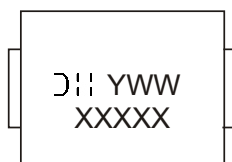
UNDER DEVELOPMENT

Ordering Information (Note 3)

| Device | Packaging | Shipping |
|--|-----------|------------------|
| TB0640M-13 TB0720M-13 TB0900M-13 TB1100M-13 TB1300M-13 TB1500M-13 TB1800M-13 TB2300M-13 TB2600M-13 TB3100M-13 TB3500M-13 | SMB | 3000/Tape & Reel |

Notes: 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



XXXXX = Product Type Marking Code
 YWW = Date Code Marking
 Y = Year ex: 2 = 2002
 WW = Week

Date Code Key

| Year | 2002 | 2003 | 2004 |
|------|------|------|------|
| Code | 2 | 3 | 4 |

UNDER DEVELOPMENT